

30V N-Channel Enhancement Mode MOSFET

Description

The AP60N03NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 60A$

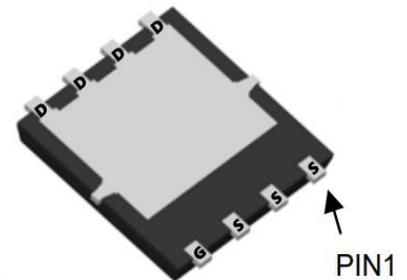
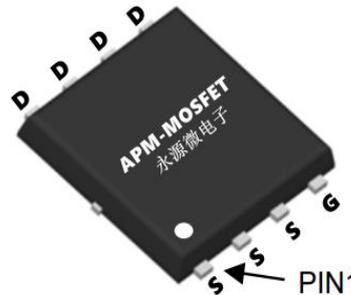
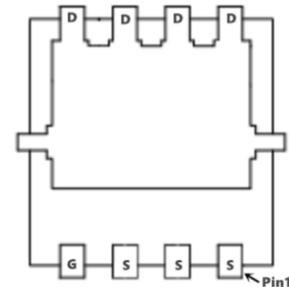
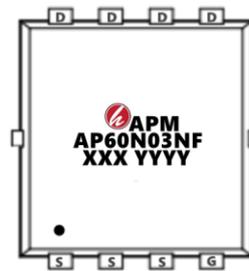
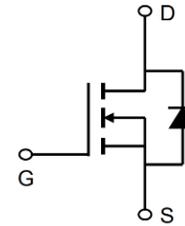
$R_{DS(ON)} < 8.5m\Omega$ @ $V_{GS}=10V$ (Type: **6.0m Ω**)

Application

BLDC

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP60N03NF	PDFN5*6-8L	AP60N03NF XXX YYYY	5000

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	40	A
IDM	Pulsed Drain Current ²	92	A
EAS	Single Pulse Avalanche Energy ³	57.8	mJ
IAS	Avalanche Current	34	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	29	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	25	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4.32	$^\circ\text{C/W}$

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Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	33	---	V
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =12A	---	6.0	8.5	mΩ
		V _{GS} =4.5V, I _D =10A	---	8.0	13	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.6	2.5	V
ΔVGS(th)	V _{GS(th)} Temperature Coefficient		---	-5.8	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =15A	---	9.8	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V, V _{GS} =4.5V, I _D =12A	---	12.8	---	nC
Q _{gs}	Gate-Source Charge		---	3.3	---	
Q _{gd}	Gate-Drain Charge		---	6.5	---	
Td(on)	Turn-On Delay Time		V _{DD} =12V, V _{GS} =10V, R _G =3.3Ω, I _D =5A	---	4.5	
T _r	Rise Time	---		10.8	---	
Td(off)	Turn-Off Delay Time	---		25.5	---	
T _f	Fall Time	---		9.6	---	
Ciss	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1317	---	pF
Coss	Output Capacitance		---	163	---	
Crss	Reverse Transfer Capacitance		---	131	---	
IS	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	46	A
ISM	Pulsed Source Current ^{2,6}		---	---	92	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V

Note :

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 20Z copper.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
3. The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=34A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

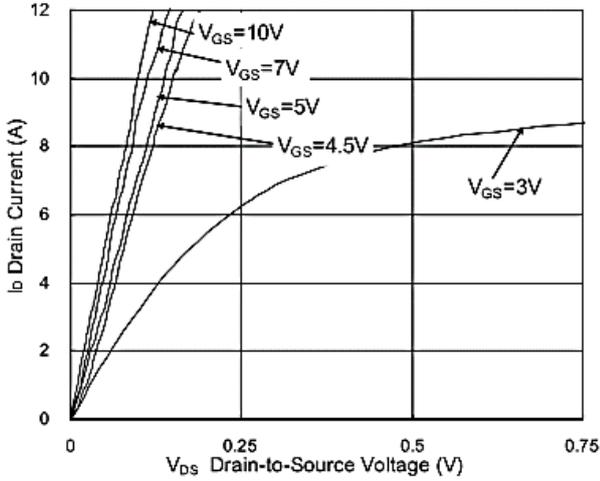


Fig.1 Typical Output Characteristics

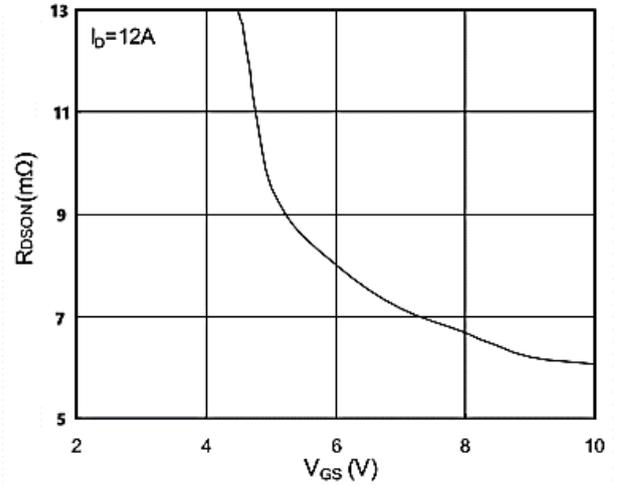


Fig.2 On-Resistance vs. G-S Voltage

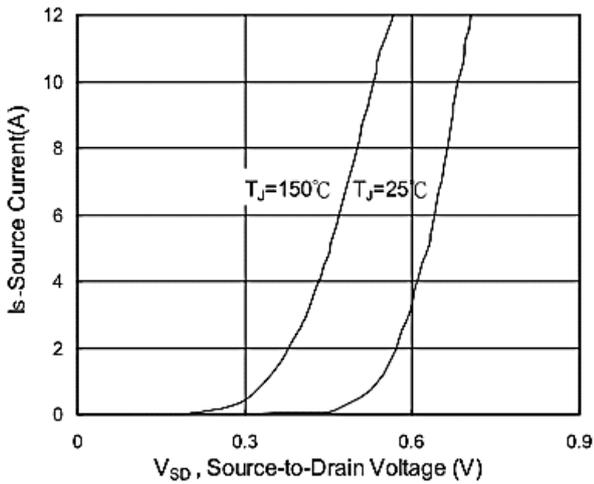


Fig.3 Forward Characteristics of Reverse

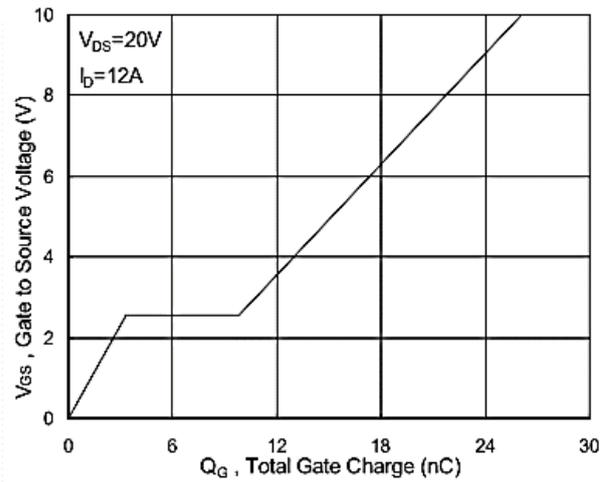


Fig.4 Gate-Charge Characteristics

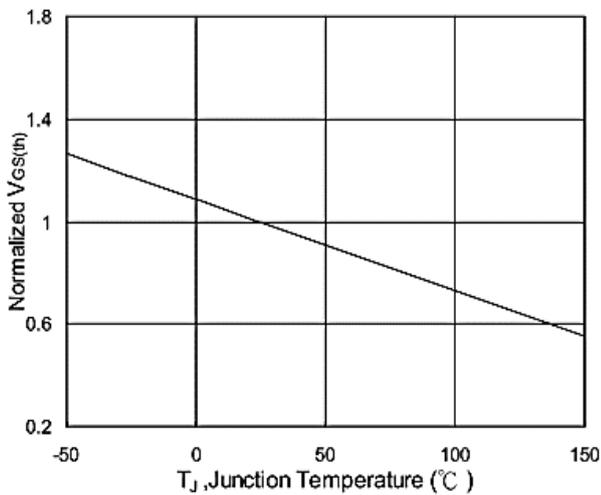


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

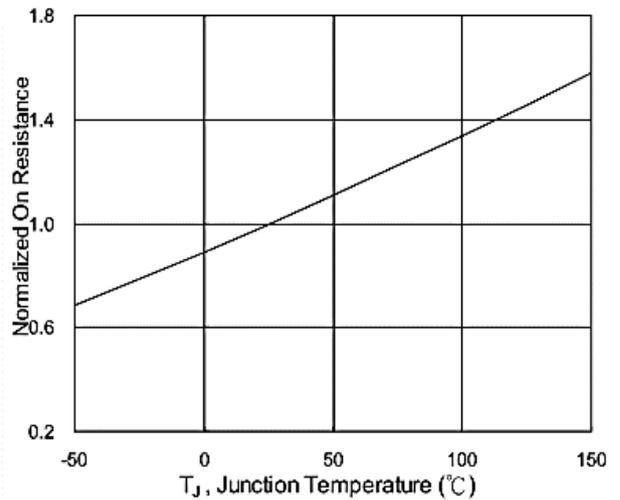


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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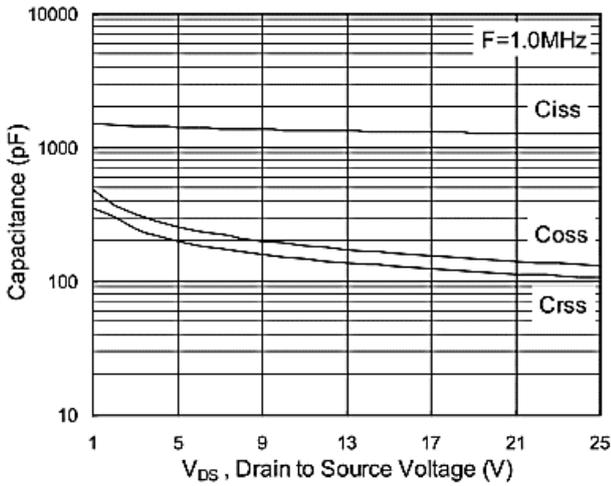


Fig.7 Capacitance

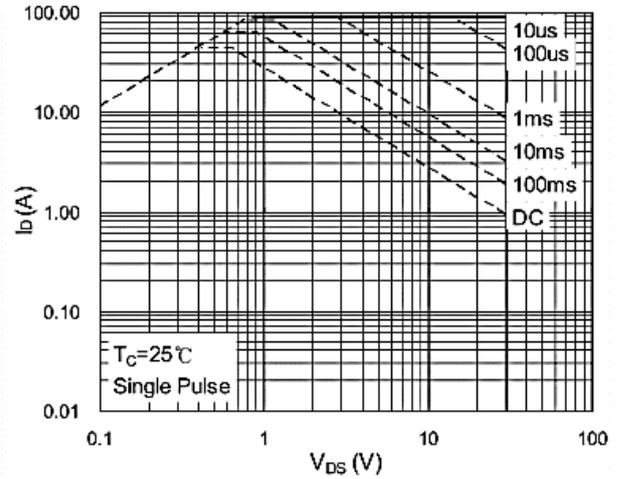


Fig.8 Safe Operating Area

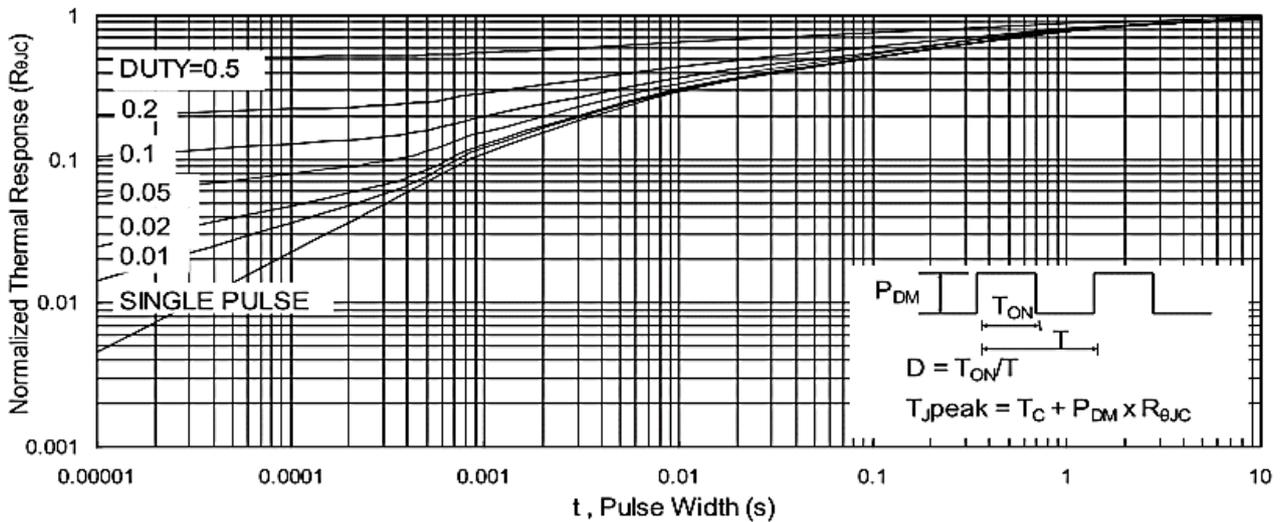


Fig.9 Normalized Maximum Transient Thermal Impedance

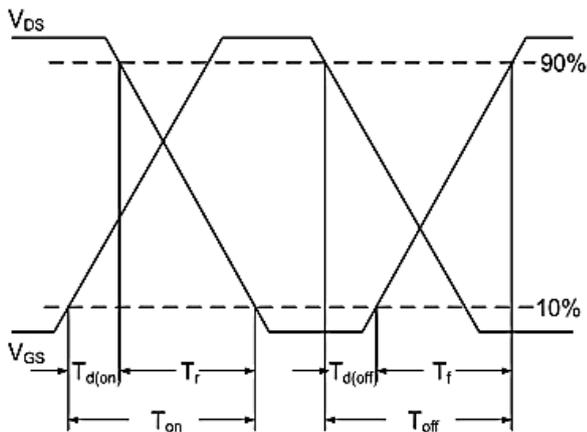


Fig.10 Switching Time Waveform

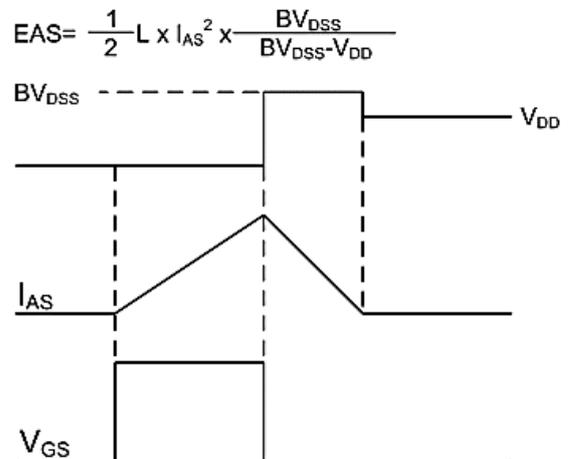
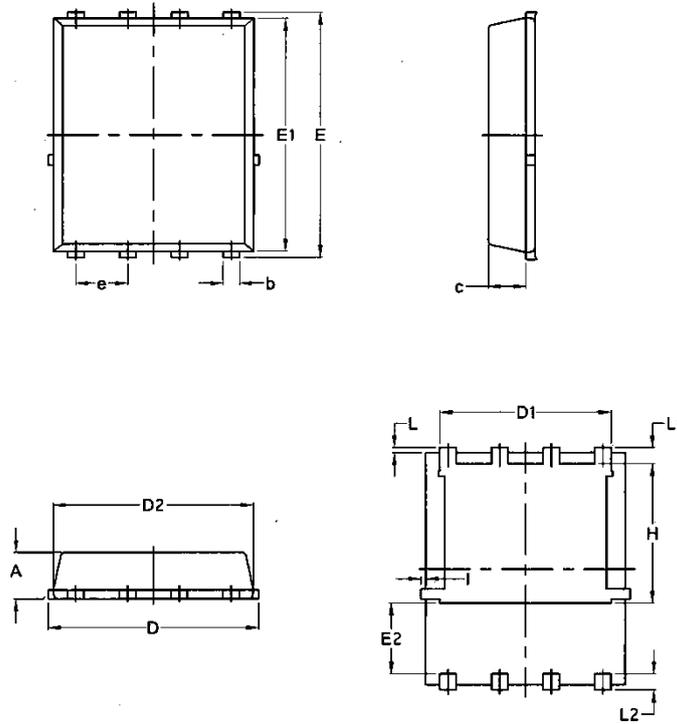


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-PDFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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Edition	Date	Change
Rve1.0	2019/4/10	Initial release
Rve1.1	2022/1/10	Reduce internal RDS

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